

Silicon PNP Power Transistors

2SB1094

DESCRIPTION

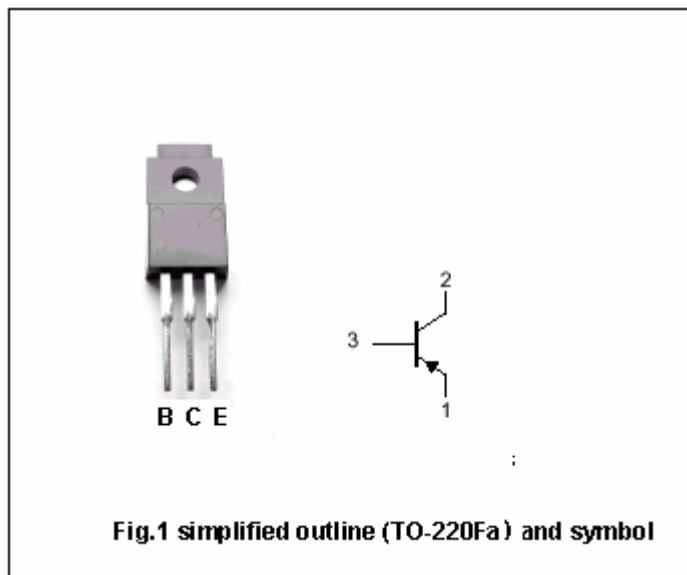
- With TO-220Fa package
- Complement to type 2SD1585

APPLICATIONS

- Ideal for power supplies or variety or in audio and other equipment

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector -emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-3	A
I_{CM}	Collector current-peak		-5	A
I_B	Base current		-0.6	A
P_C	Collector power dissipation	$T_a=25$	2.0	W
		$T_C=25$	15	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CE0}	Collector-emitter voltage	$I_C = -30\text{mA}$; $I_B = 0$	-60			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -2\text{A}$; $I_B = -0.2\text{A}$			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = -2\text{A}$; $I_B = -0.2\text{A}$			-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB} = -60\text{V}$; $I_E = 0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB} = -7\text{V}$; $I_C = 0$			-10	μA
h_{FE-1}	DC current gain	$I_C = -50\text{mA}$; $V_{CE} = -5\text{V}$	20			
h_{FE-2}	DC current gain	$I_C = -0.5\text{A}$; $V_{CE} = -5\text{V}$	40		200	
f_T	Transition frequency	$I_C = -0.1\text{A}$; $V_{CE} = -5\text{V}$		20		MHz
C_{OB}	Collector output capacitance	$f = 1\text{MHz}$; $V_{CB} = -10\text{V}$		70		pF

◆ h_{FE-2} Classifications

M	L	K
40-80	60-120	100-200

